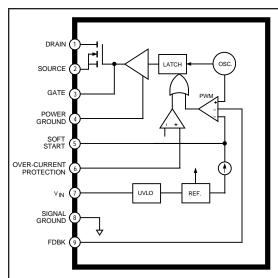
# OFF-LINE SWITCHING REGULATORS – WITH POWER MOSFET OUTPUT



Dwg. PK-0

#### **ARSOLUTE MAXIMUM RATINGS**

ABSOLUTE MAXIMUM RATI	NGS
Supply Voltage, V <sub>IN</sub>	. 35 V
Drain-Source Voltage, V <sub>DS</sub>	800 V
Drain Current, I <sub>D</sub>	
continuous	. ±5 A
single pulse, $t_w \le 1$ ms	±20 A
A alasaka Essas E	
single pulse4	00 mJ
Gate-Source Voltage, V <sub>GS</sub>	±20 V
Gate-Drive Current Range,	
I <sub>G</sub> 0.7 A to	+1.5 A
Over-Current Protection Voltage Ran	ge,
V <sub>OCP</sub> 0.3 V to	+4.0 V
Insulation RMS Voltage,	,
V <sub>WM(RMS)</sub>	2000 V
Package Power Dissipation,	
P <sub>D</sub> <b>See</b>	Graph
FET Channel Temperature, T <sub>1</sub> +	150°C
Internal Frame Temperature, T <sub>F</sub> +	125°C
Operating Temperature Range,	
T <sub>A</sub> 20°C to +	125°C
Storage Temperature Range,	
T <sub></sub> -30°C to +	125°C

These devices are specifically designed to meet the requirements for increased integration and reliability in off-line flyback (STR-S6411) and forward (STR-S6411F) converters operating in a fixed-frequency PWM mode. Each device incorporates the primary control and drive circuits with an avalanche-rated high-voltage power MOSFET. Crucial system parameters such as switching frequency and maximum duty cycle are fixed during manufacture. The STR-S6411 and STR-S6411F differ only in their maximum duty cycle. Control circuit decoupling and layout are optimized within each device.

Cycle-by-cycle and average-current limiting, soft start, undervoltage lockout with hysteresis, and thermal shutdown protect the device during all normal and overload conditions. The performance and reliability of these devices, and their variable-frequency counterparts, has been proven in substantial volume production.

The requirements of high dielectric isolation and low transient thermal impedance and steady-state thermal resistance are satisfied in an over-molded, 9-pin single in-line power package.

#### **FEATURES**

- PWM Flyback Conversion or Forward Conversion
- Output Power to 250 W
- Pulse-by-Pulse Current Limiting
- Fixed-Frequency 100 kHz PWM
- Avalanche-Rated Power MOSFET Switch
- Soft Start
- Internal Under-Voltage Lockout and Thermal Shutdown
- Low External Component Count
- Over-Molded SIP with Isolated Heat Spreader

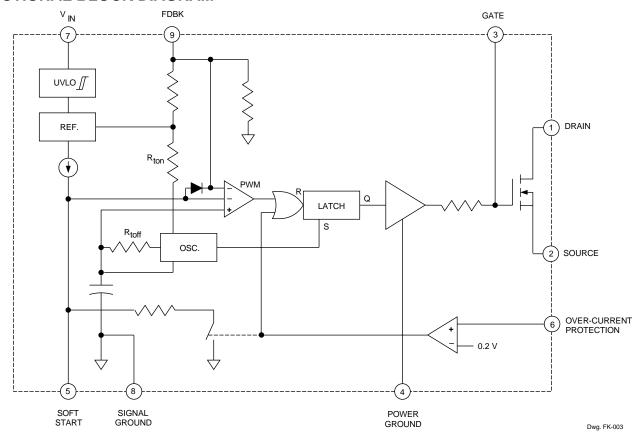
Always order by complete part number:

STR-S6411 or STR-S6411F





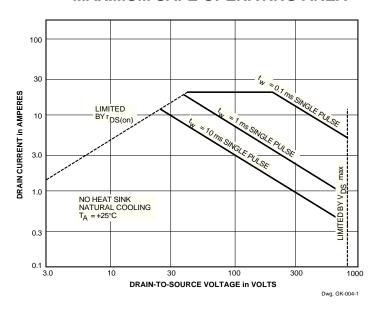
#### **FUNCTIONAL BLOCK DIAGRAM**



#### ALLOWABLE PACKAGE POWER DISSIPATION

# 60 62 W MOUNTING SURFACE TEMPERATURE RECOMMENDED MAX. FRAME TEMP. = +100°C LIMITED BY FRAME TEMP. = +125°C MAX. TEMPERATURE in °C Dwg. GK-003

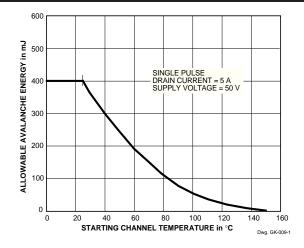
#### **MAXIMUM SAFE OPERATING AREA**







#### ALLOWABLE AVALANCHE ENERGY

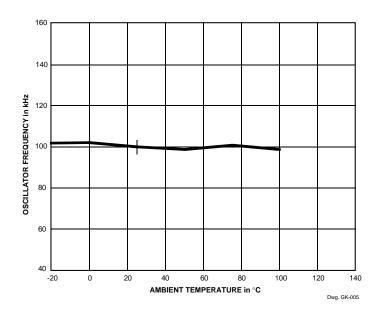


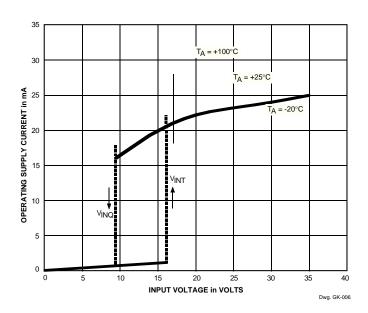
# ELECTRICAL CHARACTERISTICS at $T_A = +25^{\circ}C$ , $V_{IN} = 17$ V, voltage measurements are referenced to Signal Ground (pin 8) (unless otherwise noted).

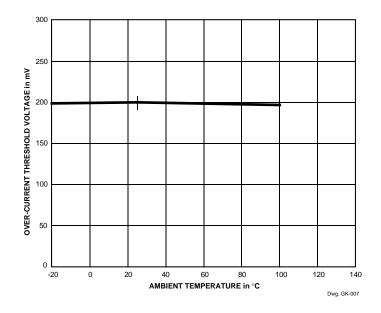
			Limits			
Characteristic	Symbol	Test Conditions	Min.	Тур.	Max.	Units
On-State Voltage	V <sub>INT</sub>	Turn-on, increasing V <sub>IN</sub>	14.4	16	17.6	V
Under-Voltage Lockout	V <sub>INQ</sub>	Turn-off, decreasing V <sub>IN</sub>	8.4	9.4	10.4	V
FET Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> = 800 V	<u> </u>	-	1.2	mA
FET ON Resistance	r <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_{D} = 3 \text{ A}$	-	1.8	2.2	Ω
Forward Transconductance	9 <sub>fs</sub>	$V_{GS} = 10 \text{ V}, I_{D} = 3 \text{ A}$	3.0	_	_	S
FET Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10 V, V <sub>GS</sub> =0 V, f=1 MHz	<u> </u>	1800	-	pF
Propagation Delay Time	t <sub>phl</sub>	Turn-on, 10% V <sub>GS</sub> to 10% V <sub>DS</sub>	<b> </b>	60	_	ns
	t <sub>plh</sub>	Turn-off, 90% V <sub>GS</sub> to 90% V <sub>DS</sub>	<b>†</b> –	140	_	ns
Oscillator Frequency	f <sub>osc</sub>		93	100	107	kHz
Maximum ON Time	t <sub>on</sub>	STR-S6411	5.1	5.7	6.5	μs
		STR-S6411F	3.8	4.5	5.2	μs
Over-Current Threshold	V <sub>OCP(th)</sub>		160	200	240	mV
OCP Current	I <sub>OCP</sub>		-250	-400	-550	μА
Feedback Current	I <sub>FDBK</sub>		-	-1.8	_	mA
Soft Start Threshold Voltage	V <sub>SS(th)</sub>		-	_	0.4	V
Soft Start Current	I <sub>SS</sub>	V <sub>SS</sub> = 0 V	-	-100	_	μΑ
Power Ground Current	I <sub>PG</sub>	t <sub>w</sub> = 200 ns	-	-1.0	-1.5	А
Supply Current	I <sub>IN(ON)</sub>	Operating	-	23	_	mA
	I <sub>IN(OFF)</sub>	Start up, V <sub>IN</sub> = 12 V	-	_	500	μΑ
Insulation RMS Voltage	V <sub>WM(RMS)</sub>	All terminals simultaneous reference	2000	_	_	V
		metal plate against backside				
Thermal Resistance	$R_{ heta JM}$	FET channel to mounting surface	-	2.0	_	°C/W

NOTES: Negative current is defined as coming out of (sourcing) the specified device terminal. Typical Data is for design information only.

#### TYPICAL CHARACTERISTICS





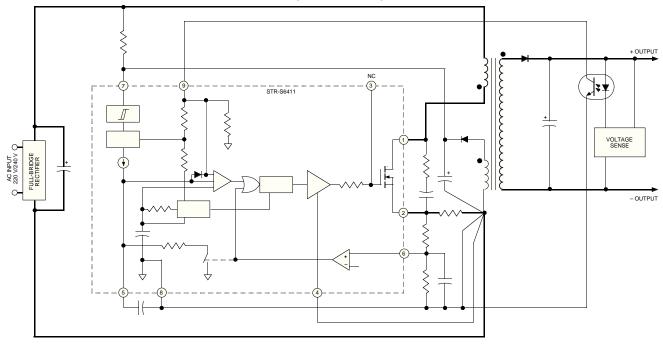






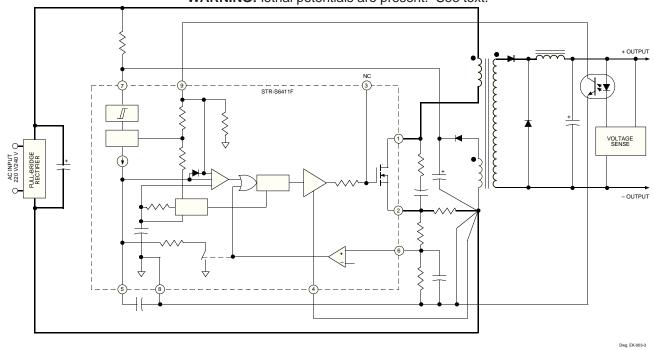
#### **TYPICAL PWM FLYBACK CONVERSION USING STR-S6411**

WARNING: lethal potentials are present. See text.



#### **TYPICAL PWM FORWARD CONVERSION USING STR-S6411F**

WARNING: lethal potentials are present. See text.



#### APPLICATIONS INFORMATION

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**WARNING** — These devices are designed to be operated at lethal voltages and energy levels.

Circuit designs that embody these components must conform with applicable safety requirements.

Precautions must be taken to prevent accidental contact with power-line potentials.

Do not connect grounded test equipment.

The use of an isolation transformer is recommended during circuit development and breadboarding.

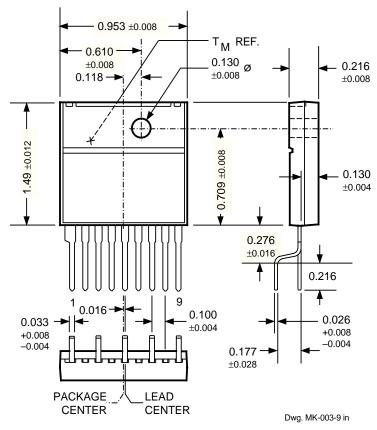
The power MOSFET outputs of these devices are similar to the International Rectifier type IRFPE40. These devices feature an excellent combination of fast switching, ruggedized device design, low on-resistance, and cost effectiveness.

Recommended mounting hardware torque:

4.34 - 5.79 lbf•ft (6 - 8 kg•cm or 0.588 - 0.784 Nm).

Recommended metal-oxide-filled, alkyl-degenerated oil base, silicone grease: Dow Corning 340, or equivalent

# Dimensions in Inches (for reference only)



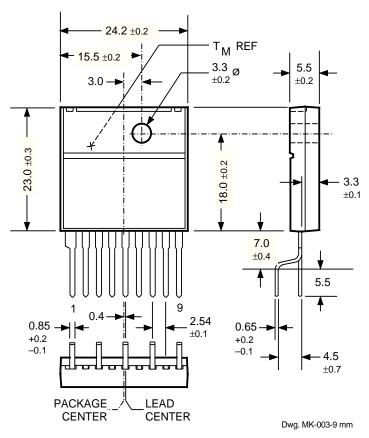
NOTE: Exact body and lead configuration at vendor's option within limits shown.





#### **Dimensions in Millimeters**

(controlling dimensions)



NOTE: Exact body and lead configuration at vendor's option within limits shown.

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# POWER CONVERSION/POWER MANAGEMENT SELECTION GUIDES

#### **SWITCHING REGULATOR PMCMs**

Part Number*	Application	Vı	Max P <sub>o</sub>	Power Switch			
3002M	5 V Switching Regulator and a 9 V Switching Regulator†	7.0-33 V		_ _	500 mA 400 mA	Bipolar Bipolar	
3004M	5 V Switching Regulator and Dual 9 V Switching Regulator	7.0-33 V	-	_ _	500 mA 2 x 400 mA	Bipolar Bipolar	
S5703	Quasi-Resonant Flyback Converter	110/120 V	140 W	500 V	6 A	Bipolar	
S5707	Quasi-Resonant Flyback Converter	85-265 V 220/240V	90 W 140 W	850 V	6 A	Bipolar	
S5708	Quasi-Resonant Flyback Converter	85-265 V 220/240 V	120 W 180 W	850 V	7.5 A	Bipolar	
F6624	Quasi-Resonant Flyback Converter	100/120 V	130 W	450 V	$0.92~\Omega$	MOSFET	
F6626	Quasi-Resonant Flyback Converter	100/120 V	190 W	450 V	$0.58~\Omega$	MOSFET	
F6628	Quasi-Resonant Flyback Converter	100/120 V	290 W	450 V	$0.35~\Omega$	MOSFET	
F6652	Quasi-Resonant Flyback Converter	85-265 V	86 W	650 V	$2.8\Omega$	MOSFET	
F6653	Quasi-Resonant Flyback Converter	85-265 V	120 W	650 V	$1.95~\Omega$	MOSFET	
F6654	Quasi-Resonant Flyback Converter	85-265 V	190 W	650 V	1.15 Ω	MOSFET	
F6656	Quasi-Resonant Flyback Converter	85-265 V	300 W	650 V	0.71 Ω	MOSFET	
F6672	Quasi-Resonant Flyback Converter	200/220 V	50 W	900 V	$7.7~\Omega$	MOSFET	
F6674	Quasi-Resonant Flyback Converter	85-265 V	76 W	900 V	4.49 Ω	MOSFET	
F6676	Quasi-Resonant Flyback Converter	85-265 V	115 W	900 V	2.81 Ω	MOSFET	
S6703	Quasi-Resonant Flyback Converter	110/120V	140 W	500 V	6 A	Bipolar	
S6704	Quasi-Resonant Flyback Converter	110/120 V	100 W	500 V	5 A	Bipolar	
S6707	Quasi-Resonant Flyback converter	85-265 V 220/240 V	90 W 140 W	850 V	6 A	Bipolar	
S6708	Quasi-Resonant Flyback Converter	85-265 V 220/240 V	120 W 180 W	850 V	7.5 A	Bipolar	
S6709	Quasi-Resonant Flyback Converter	85-265 V 220/240 V	160 W 220 W	850 V	10 A	Bipolar	
8033S	3.3 V Switching Regulator	5.5-28 V	_	_	3 A	Bipolar	
8050S	5.0 V Switching Regulator	7.0-40 V	_	_	3 A	Bipolar	
8090S	9.0 V Switching Regulator	12-40V	_	_	3 A	Bipolar	
8120S	12 V Switching Regulator	15-40 V	_	_	3 A	Bipolar	
8150S	15 V Switching Regulator	18-40 V	_	_	3 A	Bipolar	

<sup>\*</sup> Complete part number includes additional characters to indicate operating temperature range and/or package style.

 $<sup>\</sup>dagger$  Also includes linear regulator output for 15.7 V at 1.0 A.

